

REMARKS

Applicants respectfully request favorable reconsideration of this application.

Applicants acknowledge with appreciation the courtesies extended during the telephonic interview conducted on July 18, 2008. Applicants respectfully submit that the substance of the interview is accurately reflected in the Interview Summary mailed July 25, 2008.

Claims 1-18 are pending.

In the Office Action, Claims 1-18 were rejected under 35 U.S.C. § 103 over Takashi in combination with Kinoshita, Kitahara, and Moyer. Applicants respectfully traverse the rejections.

Independent Claims 1, 6 and 10 recite, *inter alia*, a semiconductor device comprising a semiconductor layer that is provided over an insulator layer having lower thermal conductivity than the semiconductor layer, and that at least a portion of a plurality of bipolar transistors are surrounded by the insulator layer and an isolation. It is apparent that the applied references do not teach or suggest this combination of features.

For example, the Office Action acknowledges at page 3, 4, and 6, that Takashi fails to teach or suggest a semiconductor layer that is provided over an insulator layer

having lower thermal conductivity than the semiconductor layer. However, it is alleged that the teachings of Kitahara cure Takashi's deficiency in this regard.

In particular, Kitahara is relied upon as allegedly teaching using an oxide 13 to provide effective isolation for bipolar transistors. However, Kitahara discloses that:

"FIG. 7 shows one practical application having a number of semiconductor elements separated by element isolation area 18 and oxide film 13. In the arrangement shown in FIG. 7, P-MOS 36, N-MOS 37 and bipolar transistors 38a, 38b are formed in the corresponding island-like element areas 19..."

Kitahara, col. 4, lines 56-61.

Referring to FIG. 7, Kitahara apparently discloses that a first transistor (BJT 38a) and a second transistor (BJT 38b) each formed in separate element areas 19. In particular, Kitahara further teaches that "element area 19, is . . . defined by element isolation area 18 and oxide film 13 so that element area 19 may be electrically isolated from the other areas." Kitahara, col. 4, lines 8-11. Thus, Kitahara appears to teach an isolation being provided for each individual transistor. In contrast, Kitahara is not understood as teaching or suggesting a semiconductor layer that is provided over an insulator layer having lower thermal conductivity than the semiconductor layer, and that at least a portion of a plurality of bipolar transistors are

surrounded by the insulator layer and an isolation, as recited in Claims 1, 6, and 10. Applicants respectfully submit that such teachings are found only in Applicants' disclosure.

The remaining secondary references are not seen to remedy the above-discussed deficiency of Takashi and Kitahara.

Applicants therefore respectfully request the outstanding rejections be withdrawn.

A Notice of Allowance is respectfully requested.  
The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 (XA-10036) any fees under 37 C.F.R. §§ 1.16 and 1.17 that may be required by this paper and to credit any overpayment to that Account. If any extension of time is required in connection with the filing of this paper and has not been separately requested, such extension is hereby requested.

Respectfully submitted,

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